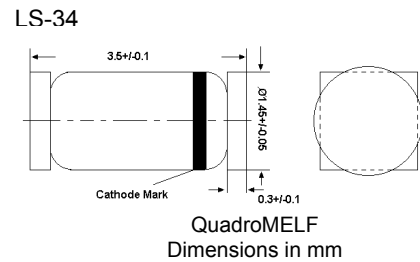


BAV201...BAV203

Silicon Epitaxial Planar Diodes

High Voltage Switching Diode

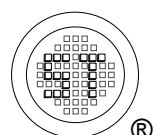


Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter		Symbol	Value	Unit
Repetitive Peak Reverse Voltage	BAV201	V_{RRM}	120	V
	BAV202		200	
	BAV203		250	
Reverse Voltage	BAV201	V_R	100	V
	BAV202		150	
	BAV203		200	
Forward Current		I_F	250	mA
Forward Peak Current (at $f = 50\text{ Hz}$)		I_{FM}	625	mA
Non-repetitive Peak Forward Surge Current at $t = 1\text{ s}$		I_{FSM}	1	A
Junction Temperature		T_j	175	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	- 65 to + 175	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter		Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$		V_F	-	-	1	V
Reverse Current at $V_R = 100\text{ V}$ at $V_R = 150\text{ V}$ at $V_R = 200\text{ V}$	BAV201	I_R	-	-	100	nA
	BAV202		-	-	100	nA
	BAV203		-	-	100	nA
Breakdown Voltage at $I_R = 100\text{ }\mu\text{A}$	BAV201	$V_{(BR)}$	120	-	-	V
	BAV202		200	-	-	V
	BAV203		250	-	-	V
Capacitance at $V_R = 0$, $f = 1\text{ MHz}$		C_D	-	1.5	-	pF
Reverse Recovery Time at $I_F = 30\text{ mA}$, $I_R = 30\text{ mA}$, $I_R = 3\text{ mA}$, $R_L = 100\text{ }\Omega$		t_{rr}	-	-	50	ns



Dated : 15/06/2009

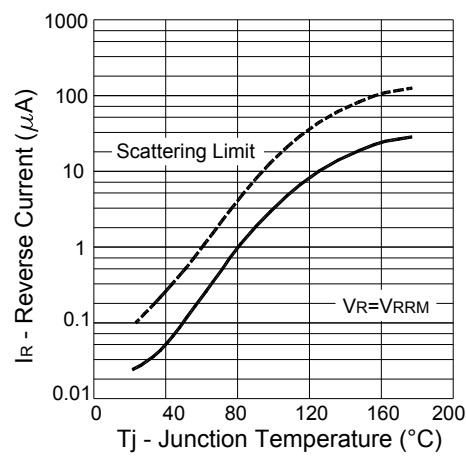


Fig 1. Reverse Current vs. Junction Temperature

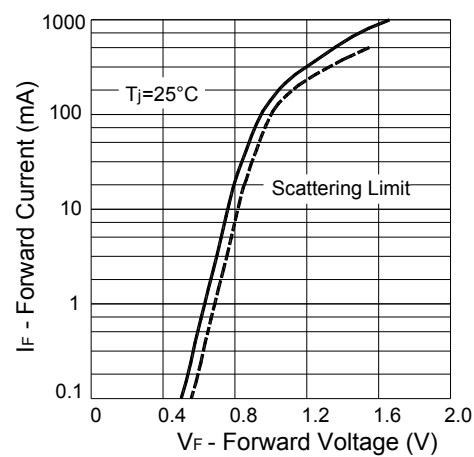


Fig 2. Forward Current vs. Forward Voltage

